

the solder hardens, and the soldering land 103 of the carrier substrate 102 is bonded to the soldering land 202 of the main substrate 201.--.

IN THE CLAIMS:

Amend claim 1 as follows:

Sub C1
A2
--1. (amended) An electrode structure of a carrier substrate of a semiconductor device for solder-bonding the semiconductor device to a main substrate, said electrode structure comprising:

a carrier substrate having a recess in a central area of a surface thereof;


a soldering land of the electrode structure arranged in the recess, said soldering land having a circumferential wall defining a hollow portion extending from said surface; and

a passage through an outer portion of said circumferential wall.--

C Amend claim 2 as follows: J

--2. (amended) The electrode structure of the carrier substrate of the semiconductor device according to claim 1, wherein said soldering land is hemispherical-shaped having a flange portion, and having a concentric hemispherical hollow portion therein, wherein said recess is hemispherical-shaped and said hemispherical portion of said soldering land fits into said hemispherical-shaped recess, and said soldering land being

fixedly attached to said carrier substrate so that said flange portion abuts said surface of said carrier substrate.--

 Amend claim 3 as follows:

--3. (amended) The electrode structure of the carrier substrate of the semiconductor device according to claim 2, wherein said passage is at least one slit portion provided in said flange portion and said circumferential wall of said soldering land adjacent to said flange portion.--

Amend claim 4 as follows:

--4. (amended) The electrode structure of said carrier substrate of said semiconductor device according to claim 1, wherein said soldering land is cylindrical having a flange portion and having a concentric cylindrical hollow portion thereinside, wherein said recess is cylindrical, said cylindrical portion of said soldering land fitting into said cylindrical recess, and said soldering land is fixedly attached to said carrier substrate so that said flange portion abuts said first surface of said carrier substrate.--

Amend claim 5 as follows:

--5. (amended) Said electrode structure of said carrier substrate of said semiconductor device according to claim 4, wherein said passage is at least one slit in said flange portion and a portion of said cylindrical wall adjacent to said flange portion.

Add the following new claims:

--8. (new) An electrode structure comprising:

Sub C2
a carrier substrate having a recess disposed on a surface thereof;

AB
a soldering land disposed in the recess, a wall of the soldering land defining an interior hollow portion, a flange extending from an upper edge of the wall; and

at least one slit through the wall and said flange providing a passage through the wall and the flange.

--9. (new) The electrode structure according to claim 8, wherein the wall is cylindrical.

--10. (new) The electrode structure according to claim 8, wherein the wall is hemispherical.

--11. (new) The electrode structure according to claim 8, wherein the flange extends above the surface of said carrier substrate.

Sub C2
--12. (new) An electrode structure comprising:

a carrier substrate having a recess disposed on a surface thereof;

a cup-shaped soldering land disposed in said recess, a wall of the soldering land defining an interior hollow portion; and

at least one slit through the wall extending from an